

# 2SD1478

## Silicon NPN epitaxial planar type darlington

For low-frequency amplification

### ■ Features

- Forward current transfer ratio  $h_{FE}$  is designed high, which is appropriate to the driver circuit of motors and printer hammer
- A shunt resistor is omitted from the driver.

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

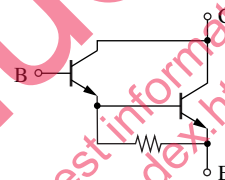
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	30	V
Collector-emitter voltage (Base open)	$V_{CEO}$	25	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_C$	500	mA
Peak collector current	$I_{CP}$	750	mA
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_J$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### ■ Package

- Code  
Mini3-G1
- Pin Name  
1: Base  
2: Emitter  
3: Collector

### ■ Marking Symbol: 2N

### ■ Internal Connection



### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

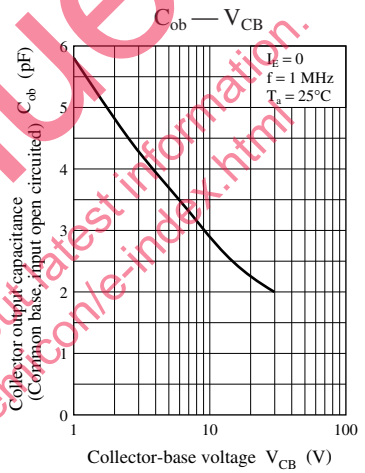
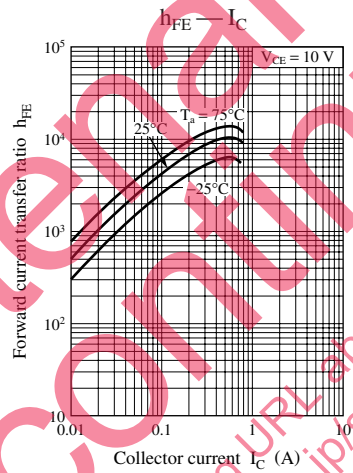
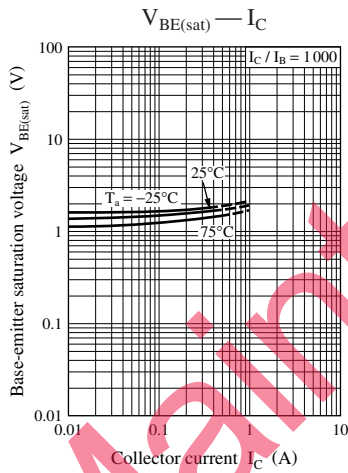
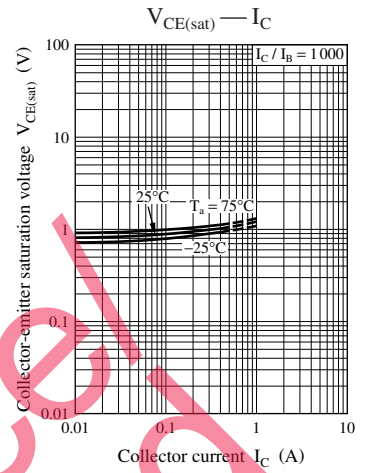
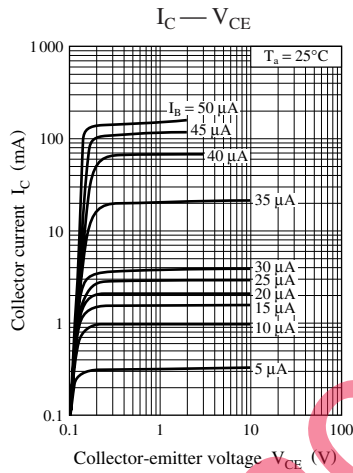
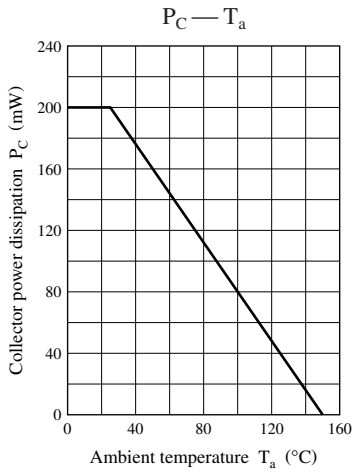
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 100 \mu\text{A}$ , $I_E = 0$	30			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1 \text{ mA}$ , $I_B = 0$	25			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 100 \mu\text{A}$ , $I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 25 \text{ V}$ , $I_E = 0$			100	nA
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 4 \text{ V}$ , $I_C = 0$			100	nA
Forward current transfer ratio <sup>*1, 2</sup>	$h_{FE}$	$V_{CE} = 10 \text{ V}$ , $I_C = 500 \text{ mA}$	4000		20000	—
Collector-emitter saturation voltage <sup>*1</sup>	$V_{CE(sat)}$	$I_C = 500 \text{ mA}$ , $I_B = 0.5 \text{ mA}$			2.5	V
Base-emitter saturation voltage <sup>*1</sup>	$V_{BE(sat)}$	$I_C = 500 \text{ mA}$ , $I_B = 0.5 \text{ mA}$			3.0	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}$ , $I_E = -50 \text{ mA}$ , $f = 200 \text{ MHz}$		200		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

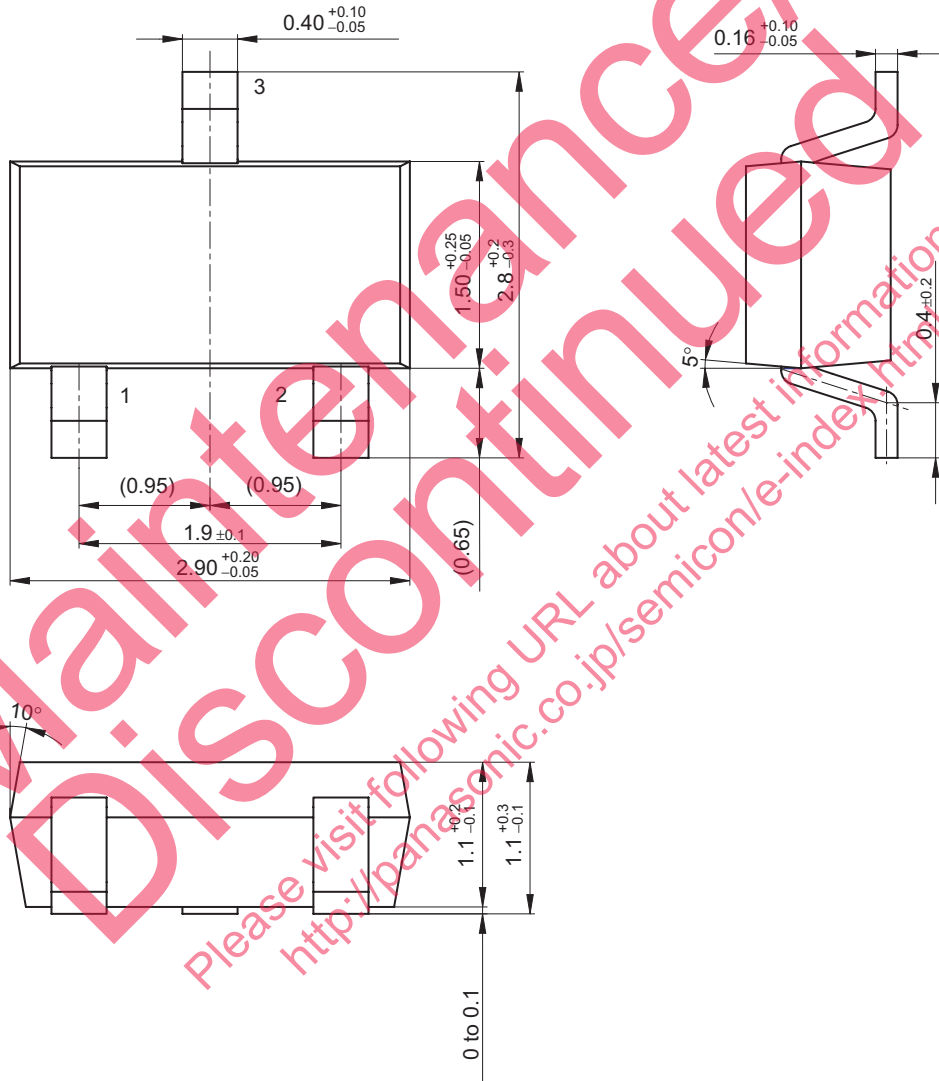
\*2: Rank classification

Rank	Q	R
$h_{FE}$	4000 to 10000	8000 to 20000



Mini3-G1

Unit: mm



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